

产品概览

NCP51530: 高性能, 700 V- 3.5/3.0 A 高压侧和低压侧 MOSFET 驱动器

欲看完整文档, 请参阅数据表。

NCP51530 是一款 700 V 高压侧和低压侧驱动器, 其高驱动能力适用于 AC-DC 电源和逆变器。NCP51530 在高运行频率下提供最佳传播延迟、低静止电流和低开关电流。因此, 此器件可实现在高频率下运行的高能效电源设计。NCP51530 采用 SOIC8 和 DFN10 封装。

特性

- High voltage range: Up to 700 V
- Very fast propagation delay (25 ns for B version)
- Matched propagation delay (7 ns Max)
- High dv/dt immunity up to 50 V/ns and negative transient immunity
- DFN10 packaging with optimized pin-out
- Fast Rise and Fall times (15 ns max)

应用

- Half and Full-bridge Converters
- Active Clamp Flyback adapters
- Motor controls Power Supply

优势

- Design margin for AC/DC design
- Suitable for high frequency operation
- Increased efficiency & Allow paralleling
- Very robust design
- Small PCB footprint, improved creepage distance and parasitic
- Suitable for heavy loads

终端产品

- Power Supply for Servers, Telecom and Industrial
- Electric power steering
- Solar inverters

器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Power Switch	Number of Outputs	Topology	Isolation Type	V _{in} Max (V)	V _{CC} Max (V)	Drive Source / Sink Typ (mA)	Rise Time (ns)	Fall Time (ns)	t _o Max (ns)	Package Type
NCP51530ADR2G	0.714	Pb-free Halide free non AEC-Q and PPAP	Active	MOSFET / IGBT	2	High-Low	Junction Isolation	700	20	3500 / 3000	8	8	60	SOIC-8
NCP51530AMNTWG	0.833	Pb-free Halide free non AEC-Q and PPAP	Active	MOSFET / IGBT	2	High-Low	Junction Isolation	700	20	3500 / 3000	8	8	60	DFN-10
NCP51530BDR2G	0.714	Pb-free Halide free non AEC-Q and PPAP	Active	MOSFET / IGBT	2	High-Low	Junction Isolation	700	20	3500 / 3000	8	8	25	SOIC-8
NCP51530BMNTWG	0.7266	Pb-free Halide free non AEC-Q and PPAP	Active	MOSFET / IGBT	2	High-Low	Junction Isolation	700	20	3500 / 3000	8	8	25	DFN-10

欲了解更多信息, 请联系您当地的销售支援 www.onsemi.cn。

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